

IC Stage Biasing

- *Avoids resistors as much as possible*
 - *Resistors take up very large area on IC chips, which is at a premium*
- *Uses transistors as biasing elements*
 - *Much more compact than resistors, and area consumption is almost negligible as compared to resistors*
- Also known as *active biasing*

- **Parameters:**

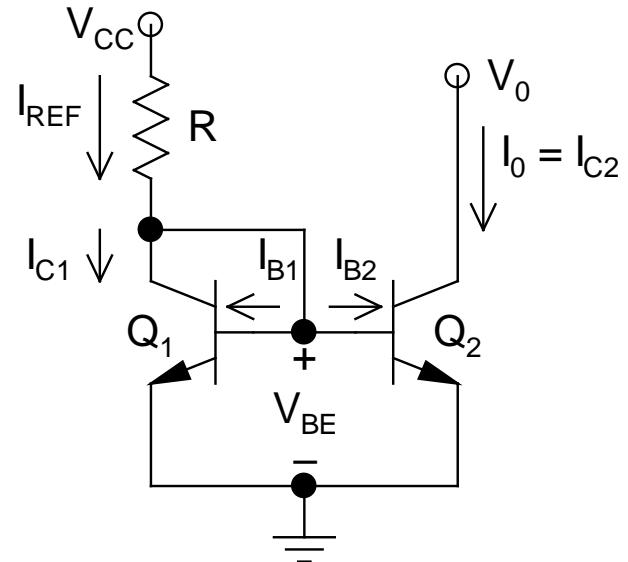
- **Output Current I_0**
 - *As per specification*
- **Output Resistance R_0**
 - $R_0 = \Delta V_0 / \Delta I_0 = dV_0 / dI_0 = v_0 / i_0$ (*ac*)
 - *As large as possible - ideally infinite*
- **Minimum Allowed Output Voltage $V_{0,min}$**
 - *As small as possible - ideally zero*
 - **Dictated by:**
 - ❖ *For BJT*: $V_{CE}(\min) = V_{CE}(SS) = 0.2$ V
 - ❖ *For MOSFET*: $V_{DS}(\min) = V_{GT}(\min) = 80$ mV

- *I_0 should be independent of power supply and temperature*
 - *Temperature and Supply Independent Biasing*
- *Should use minimum number of circuit elements*
 - *Economization of space*
- *Should not affect frequency response*
- It is *almost impossible to satisfy all these constraints simultaneously*
 - *Look for optimization*

Current Sources/Sinks

- Also known as *Current Mirrors* (CM)
- Can be used for *biasing* as well as *load elements* (known as *active load*)
- Designed based on *required specifications*
- *Two sources of errors:*
 - *Systematic*: *Even when devices are matched*
 - *Random*: *When there is a random mismatch between devices*

- *Simple npn CM:*
 - Q_1 has its ***B and C shorted***
 - *Can never saturate* ($V_{BC} = 0$)
 - Known as *diode-connected BJT*
 - Q_1 and Q_2 have ***same V_{BE}***
 - $I_{REF} = \text{Reference Current}$
 $= (V_{CC} - V_{BE})/R$
 - $I_0 = \text{Output Current} = I_{C2}$
 - $V_0 = \text{Output Voltage}$
 - *Variable, depends on the load connected to it*



➤ *General Analysis:*

$$I_{REF} = I_{C1} + I_{B1} + I_{B2} = I_{C1} \left(1 + \frac{1}{\beta_1} \right) + \frac{I_{C2}}{\beta_2}$$

➤ Now:

$$V_{BE} = V_T \ln \left(\frac{I_{C2}}{I_{S2}} \right) = V_T \ln \left(\frac{I_{C1}}{I_{S1}} \right)$$

$$\Rightarrow I_{C2} = K I_{C1} \quad (K = I_{S2}/I_{S1})$$

➤ Thus:

$$I_{REF} = I_{C2} \left[\frac{1}{\beta_2} + \frac{1}{K} \left(1 + \frac{1}{\beta_1} \right) \right]$$

➤ ***Finally:***

$$I_0 = \frac{I_{\text{REF}}}{\frac{1}{\beta_2} + \frac{1}{K} \left(1 + \frac{1}{\beta_1} \right)}$$

- This is the *exact expression* of I_0 , *without making any assumptions/approximations whatsoever*
- The *only assumption* so far is that we have *neglected Early effect*, which we would include soon

➤ Now, we *make approximations/assumptions*:

1. $\beta_1 = \beta_2 = \beta$:

$$\Rightarrow I_0 = \frac{KI_{\text{REF}}}{1 + \frac{1+K}{\beta}}$$

2. $I_{S1} = I_{S2} = I_S$ ($K = 1$):

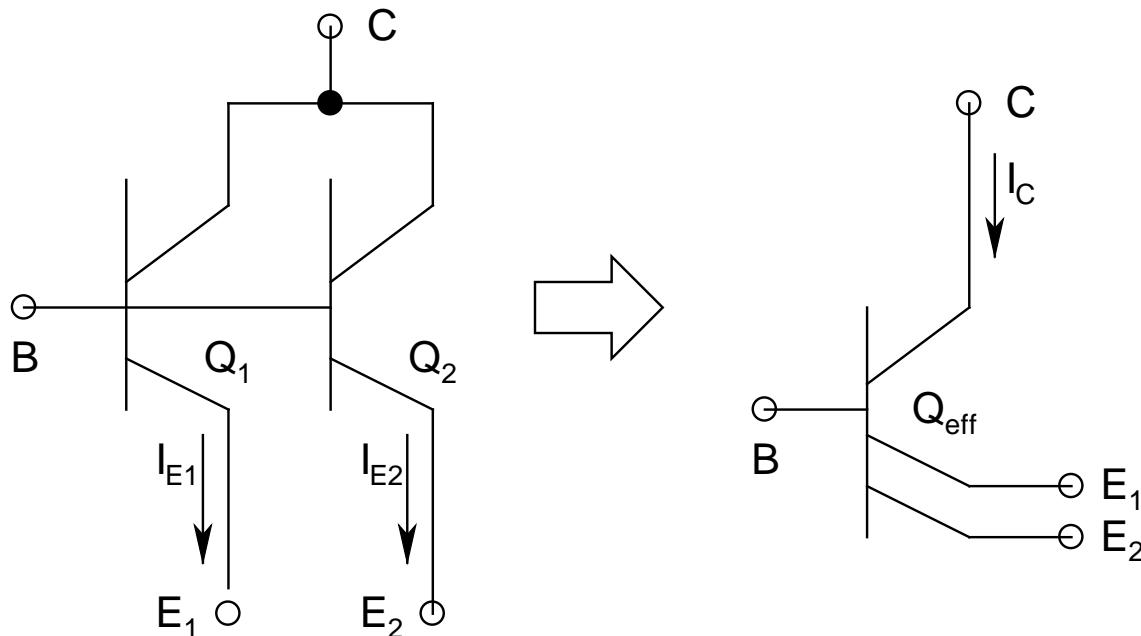
$$\Rightarrow I_0 = \frac{I_{\text{REF}}}{1 + 2/\beta}$$

3. And finally $\beta \gg 2$:

$$\Rightarrow I_0 = I_{\text{REF}} \Rightarrow \textcolor{teal}{\textit{Current Mirror!}}$$

- For this to happen, Q_1 and Q_2 must have *same β* ($>> 2$), and *same I_S*
- If two BJTs have *same β , I_S , and V_A* , they are known as a *matched pair*
- If $I_{S1} \neq I_{S2}$ and/or $\beta_1 \neq \beta_2$, then $I_0 \neq I_{\text{REF}}$
 - Leads to *random error (process induced)*
- If $\beta_1 = \beta_2$, but $I_{S1} \neq I_{S2}$, then $I_0 = KI_{\text{REF}}$
 - *K or 1/K can only be integers*
 - *I_0 and I_{REF} become integer multiples of each other*

- **Multi-Emitter BJT:**



- $I_{S1} = I_{S2} \Rightarrow I_{E1} = I_{E2} = I_E \Rightarrow I_C \approx 2I_E$
 - *This does not imply that $\alpha = 2$, since there are two emitters*

- *Systematic Error:*

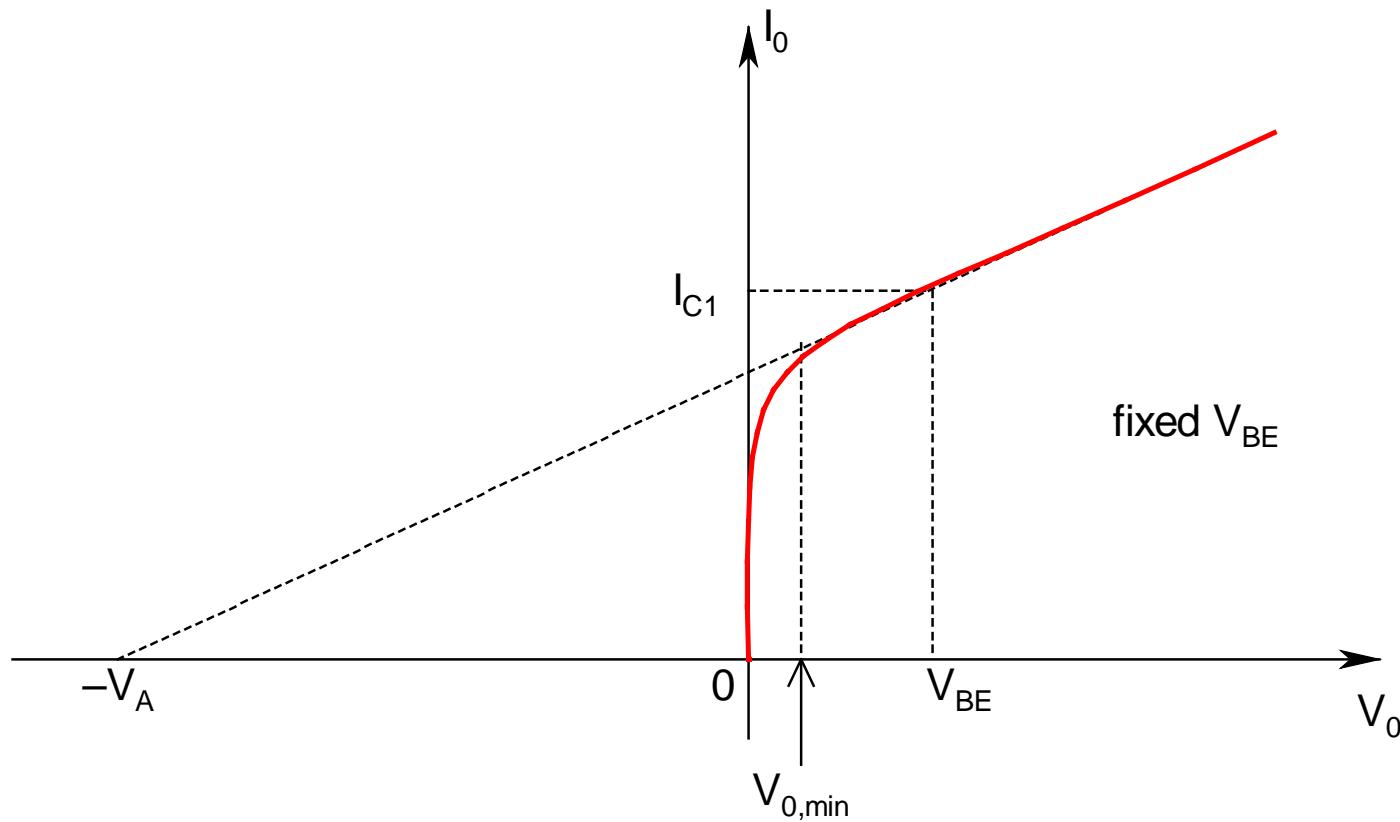
- Even if Q_1 and Q_2 are perfectly matched and $\beta \gg 2$, still I_0 may not equal I_{REF} !
- *Recall:*

$$I_C = I_S [\exp(V_{BE}/V_T)] (1 + V_{CE}/V_A)$$

- *Thus:*

$$\frac{I_{C2}}{I_{C1}} = \frac{I_0}{I_{C1}} = \frac{1 + V_{CE2}/V_A}{1 + V_{CE1}/V_A} = \frac{1 + V_0/V_A}{1 + V_{BE}/V_A}$$

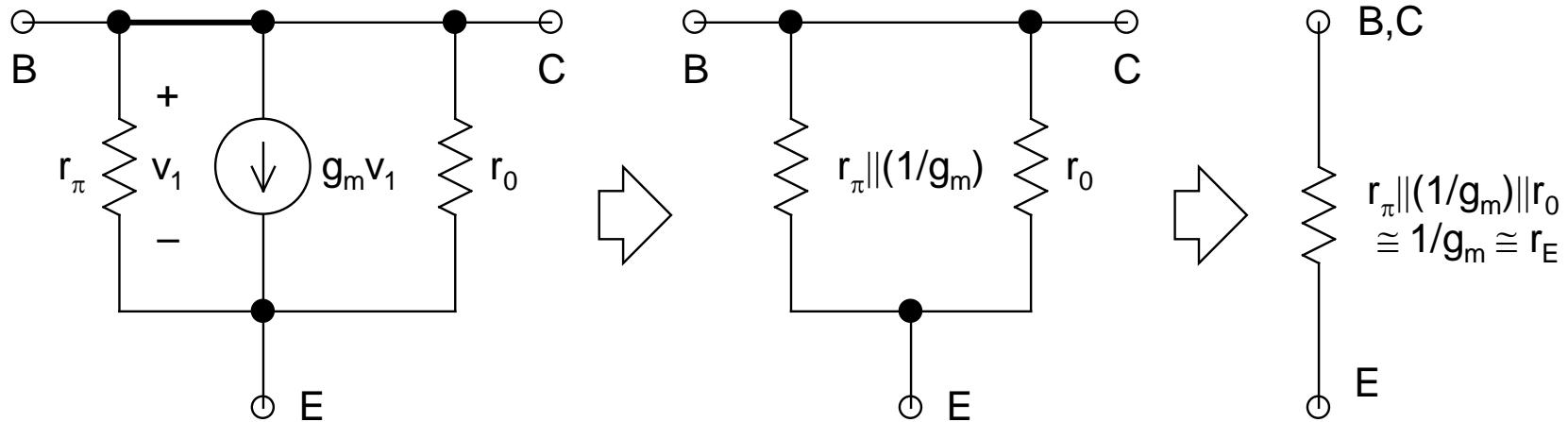
- Therefore, $I_0 = I_{C1}$ only when $V_0 = V_{BE}$



$$V_{0,min} = V_{CE2(SS)} = 0.2 \text{ V}$$

- ***Output Resistance R_0 :***

➤ First, *investigate Q_1*



➤ The *small-signal equivalent* consists simply of r_E , which is the same as that for a *diode*

- Hence the name *diode-connected transistor*

- *Algorithm to find R_0 :*
 - *Short all independent DC voltage sources*
 - *Open all independent DC current sources*
 - *Replace the active device by its low-frequency hybrid- π model*
 - *Excite the output terminal by a test voltage source (ac) v_t*
 - *Find the current (ac) i_t drawn from v_t*
 - *Then, $R_0 = v_t/i_t$*

- *For the complete circuit:*

➤ *Left part of the circuit has no source*

$$\Rightarrow v_2 = 0$$

$$\Rightarrow g_{m2}v_2 = 0$$

➤ Thus, $R_o = v_t/i_t = r_{02} = V_{A2}/I_0$

➤ For a *good current source*, R_o should be as large as possible (ideally infinite)

⇒ V_{A2} should be as large as possible and/or I_0 should be as small as possible

